

PATENT

Case Docket No. IMEC197.001CP1
Date: January 21, 2004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : Solanki, Chetan Singh
Appl. No. : 10/670,754
Filed : September 24, 2003
For : METHOD AND APPARATUS
FOR CONTINUOUS
FORMATION AND LIFT-OFF
OF POROUS SILICON
LAYERS
Examiner : Unassigned
Group Art Unit : 3661

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

January 21, 2004

(Date)

Mark M. Abumeri, Reg. No. 43,458

TRANSMITTAL LETTER

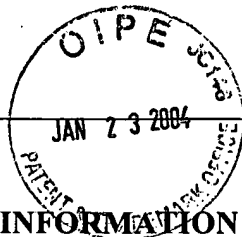
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed for filing in the above-identified application are:

- (X) An Information Disclosure Statement.
- (X) A PTO Form 1449 listing thirteen (13) references.
- (X) The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment, to Account No. 11-1410.
- (X) Return prepaid postcard.

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INFORMATION DISCLOSURE STATEMENT

Applicant(s) : Solanki, Chetan Singh

Examiner: Unassigned

Appl. No. : 10/670,754

Group Art Unit: 3661

Filed : September 24, 2003

For : METHOD AND APPARATUS FOR
CONTINUOUS FORMATION AND LIFT-
OFF OF POROUS SILICON LAYERS

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing thirteen (13) references that are of record in U.S. patent application No. 09/802,756, filed March 9, 2001, which issued November 18, 2003 as U.S. Patent No. 6,649,485, and is the parent of this continuation-in-part application, and is relied upon for an earlier filing date under 35 U.S.C. § 120. Copies of the references are not submitted pursuant to 37 C.F.R. § 1.98(d).

This Information Disclosure Statement is being filed before the receipt of a first Office Action on the merits, and presumably no fee is required in accordance with 37 C.F.R. § 1.97(b)(3). If a first Office Action on the merits was mailed before the mailing date of this Statement, the Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) to Deposit Account No. 11-1410.

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated:

January 21, 2004

By:

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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. IMEC197.001CP1	APPLICATION NO. 10/670,754
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Solanki, Chetan Singh	
		FILING DATE September 24, 2003	GROUP 3661

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1	5,206,523	04/27/93	Goesele, et al.			
	2	6,326,280 B1	12/04/01	Tayanaka			
	3	6,331,208 B1	12/18/01	Nishida, et al.			
	4	6,350,702 B2	02/26/02	Sakaguchi, et al.			

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	5	EP 0 226 091 A2	06/24/87	EUROPE			X	
	6	EP 0 797 258 A2	09/24/97	EUROPE			X	
	7	EP 0 975 012 A2	01/26/00	EUROPE			X	

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	8	Bender, et al., "Morphological properties of porous-Si layers for n ⁺ -emitter applications", Applied Surface Science, Vol. 47, pp. 187-200, (1999).
	9	Billat, et al., "Influence of etch stops on the microstructure of porous silicon layers", Thin Solid Films, Vol. 297, pp. 22-25, (1997).
	10	Ookubo, et al., "Microscope observation of a self-standing film of porous silicon", Materials Science and Engineering, Vol. B20, pp. 324-327, (1993).
	11	Rinke, et al., "Quasi-monocrystalline silicon for thin-film devices", Applied Physics A, 68, pp. 705-707, (1999).
	12	Tayanaka, et al., "Thin-film crystalline silicon solar cells obtained by separation of a porous silicon sacrificial layer", 2 nd World Conference and Exhibition on Photovoltaic Solar Energy Conversion, Vienna, Austria, 1272 (July 6-10, 1998).
	13	European Search Reports for European Application No. EP 00 87 0040, dated August 28, 2000.

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EXAMINER	DATE CONSIDERED
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	